

Photodiode 100 mm² with Integrated Thin Film Filter



FEATURES

- 100 mm² Square Active Area
- Responsivity @ 13.5 nm 0.09 A/W
- Detection Range 12 nm to 18 nm
- Shipped with Protective Cover

Electro-Optical Characteristics at 25°C

Parameters	Test Conditions	Min	Тур	Max	Units
Active Area	10 mm x 10 mm		100		mm ²
Responsivity	@ 13.5 nm	0.08	0.09	0.1	A/W
Dark Current	V _R = 15 V		8	25	nA
Reverse Breakdown Voltage, V_R	1 _R = 1 μA	25			Volts
Capacitance, C	V _R = 0 V	0.8	1	1.2	nF
Capacitance, C	V _R = 12 V	220	260	350	pF
Response Time, tr	RL = 50 Ω, V _R = 12 V		30		nsec

Thermal Parameters

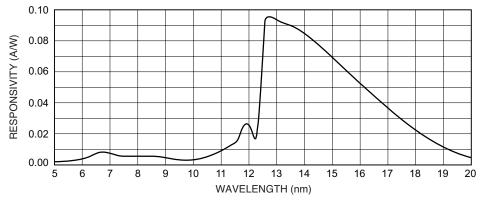
Storage and Operating Temperature Range	Units		
Ambient	-10° to 40°C		
Nitrogen or Vacuum	–20 to 80°C		
Lead Soldering Temperature*	260°C		

*0.080" from case for 10 seconds.

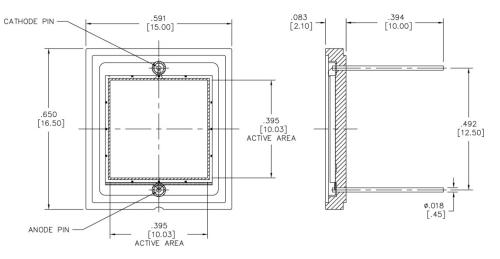


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Typical Responsivity at 25°C



Package Information



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.